

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

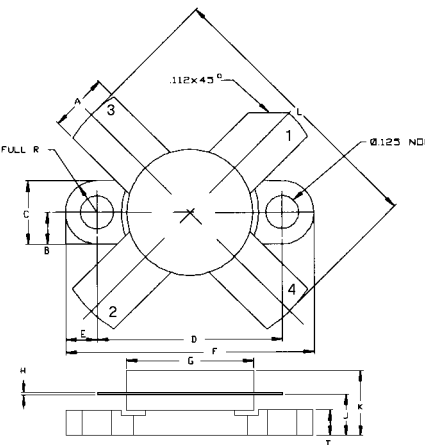
The **ASI S50-28** is Designed for Class AB or C, Common Emitter Linear HF Communications Applications.

FEATURES INCLUDE:

- High Power Gain
- Emitter Ballasting

MAXIMUM RATINGS

I_C	9.0 A
V_{CB}	65 V
P_{DISS}	117 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	1.7 °C/W

PACKAGE STYLE .500" 4L FLG		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
	A	.220/5,59 .230/5,84
	B	.125/3,18
	C	.245/6,22 .255/6,48
	D	.720/18,28 .730/18,54
	E	.125/3,18
	F	.970/24,64 .980/24,89
	G	.495/12,57 .505/12,83
	H	.003/0,08 .007/0,18
	I	.090/2,29 .110/2,79
	J	.160/4,06 .175/4,45
	K	.280/7,11
	L	1.050/26,67

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 200 mA	65			V
BV_{CEO}	I _C = 200 mA	35			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CBO}	V _{CB} = 30 V			2.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 500 mA	10		200	---
C_{ob}	V _{CB} = 30 V f = 1.0 MHz			150	pF
P_{out}	V _{CE} = 28 V P _{in} = 1.0 W fo = 30 MHz	50	60		W
P_G		17	18		dB
h_C			65		%